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THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Tamotsu OWADA et al.**

Group Art Unit: **2811**

Application No.: **10/694,826**

Examiner: **Nitin Parekh**

Filed: **October 29, 2003**

Confirmation No.: **9457**

For: **SILICON OXYCARBIDE, GROWTH METHOD OF SILICON  
OXYCARBIDE LAYER, SEMICONDUCTOR DEVICE AND  
MANUFACTURE METHOD FOR SEMICONDUCTOR DEVICE**

Attorney Docket Number: **032060**

Customer Number: **38834**

**RESPONSE UNDER 37 C.F.R. § 1.111**

Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

Date: May 9, 2005

Sir:

In response to the Office Action dated February 8, 2005, Applicants amend the claims as follows and submit the following remarks.

Amendments to the Claims begin on page 2 of this paper.

Remarks/Arguments begin on page 10 of this paper.